

# DMC204B3

## Silicon NPN epitaxial planar type

For general amplification

### ■ Features

- High forward current transfer ratio  $h_{FE}$  with excellent linearity
- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

### ■ Basic Part Number

DSC2501 + DSC2001 (Individual)

### ■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

### ■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	$V_{CBO}$	60	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	50	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	7	V
	Collector current	$I_C$	100	mA
	Peak collector current	$I_{CP}$	200	mA
Tr2	Collector-base voltage (Emitter open)	$V_{CBO}$	25	V
	Collector-emitter voltage (Base open)	$V_{CEO}$	20	V
	Emitter-base voltage (Collector open)	$V_{EBO}$	12	V
	Collector current	$I_C$	0.5	A
	Peak collector current	$I_{CP}$	1	A
Overall	Total power dissipation	$P_T$	300	mW
	Junction temperature	$T_j$	150	$^\circ\text{C}$
	Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

### ■ Package

#### • Code

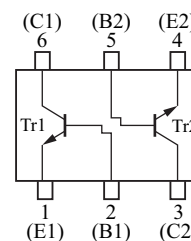
Mini6-G4-B

#### • Pin Name

- |                    |                    |
|--------------------|--------------------|
| 1: Emitter (Tr1)   | 4: Emitter (Tr2)   |
| 2: Base (Tr1)      | 5: Base (Tr2)      |
| 3: Collector (Tr2) | 6: Collector (Tr1) |

### ■ Marking Symbol: C6

### ■ Internal Connection



■ Electrical Characteristics  $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

• Tr1

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = 10 \mu\text{A}, I_{\text{E}} = 0$	60			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = 2 \text{ mA}, I_{\text{B}} = 0$	50			V
Emitter-base voltage (Collector open)	$V_{\text{EBO}}$	$I_{\text{E}} = 10 \mu\text{A}, I_{\text{C}} = 0$	7			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = 20 \text{ V}, I_{\text{E}} = 0$			0.1	$\mu\text{A}$
Collector-emitter cutoff current (Base open)	$I_{\text{CEO}}$	$V_{\text{CE}} = 10 \text{ V}, I_{\text{B}} = 0$			100	$\mu\text{A}$
Forward current transfer ratio	$h_{\text{FE}}$	$V_{\text{CE}} = 10 \text{ V}, I_{\text{C}} = 2 \text{ mA}$	210		460	—
Collector-emitter saturation voltage	$V_{\text{CE(sat)}}$	$I_{\text{C}} = 100 \text{ mA}, I_{\text{B}} = 10 \text{ mA}$		0.13	0.3	V
Transition frequency	$f_{\text{T}}$	$V_{\text{CE}} = 10 \text{ V}, I_{\text{C}} = 2 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	$C_{\text{ob}}$	$V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = 0, f = 1 \text{ MHz}$		1.5		pF

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

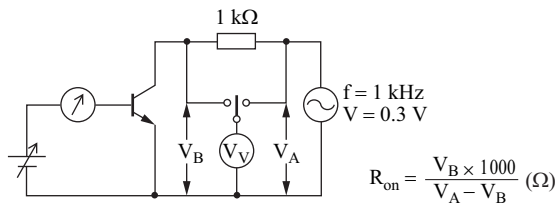
• Tr2

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	$V_{\text{CBO}}$	$I_{\text{C}} = 10 \mu\text{A}, I_{\text{E}} = 0$	25			V
Collector-emitter voltage (Base open)	$V_{\text{CEO}}$	$I_{\text{C}} = 1 \text{ mA}, I_{\text{B}} = 0$	20			V
Emitter-base voltage (Collector open)	$V_{\text{EBO}}$	$I_{\text{E}} = 10 \mu\text{A}, I_{\text{C}} = 0$	12			V
Collector-base cutoff current (Emitter open)	$I_{\text{CBO}}$	$V_{\text{CB}} = 25 \text{ V}, I_{\text{E}} = 0$			100	nA
Forward current transfer ratio	$h_{\text{FE}}$	$V_{\text{CE}} = 2 \text{ V}, I_{\text{C}} = 0.5 \text{ A}$	200		800	—
Collector-emitter saturation voltage *1	$V_{\text{CE(sat)}}$	$I_{\text{C}} = 0.5 \text{ A}, I_{\text{B}} = 20 \text{ mA}$		0.18	0.40	V
Base-emitter saturation voltage *1	$V_{\text{BE(sat)}}$	$I_{\text{C}} = 0.5 \text{ A}, I_{\text{B}} = 50 \text{ mA}$			1.2	V
Transition frequency	$f_{\text{T}}$	$V_{\text{CE}} = 10 \text{ V}, I_{\text{C}} = 50 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	$C_{\text{ob}}$	$V_{\text{CB}} = 10 \text{ V}, I_{\text{E}} = 0, f = 1 \text{ MHz}$		6		pF
ON resistance *2	$R_{\text{on}}$			1.0		$\Omega$

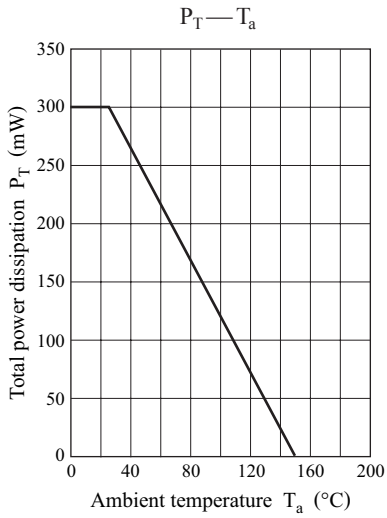
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*1: Pulse measurement

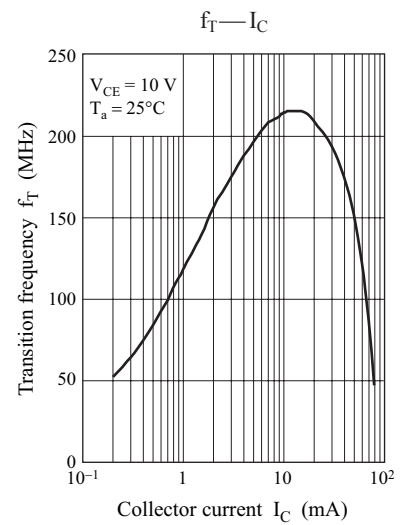
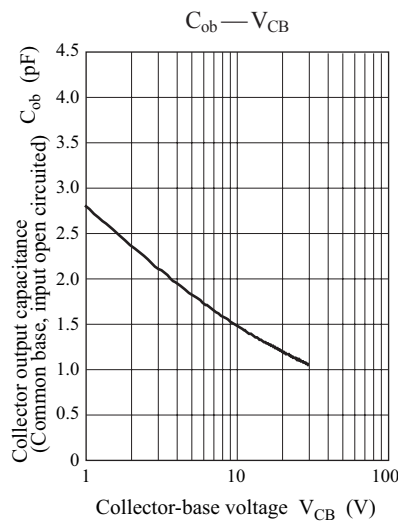
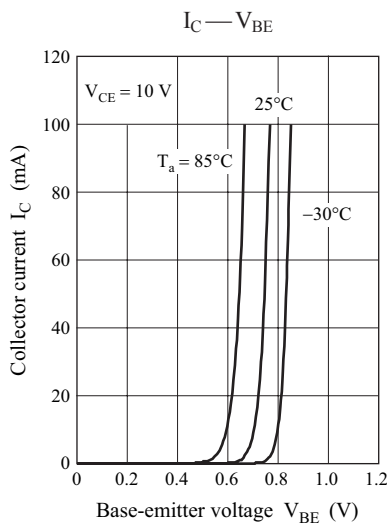
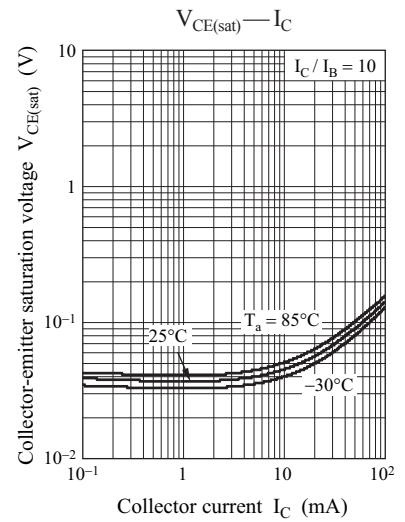
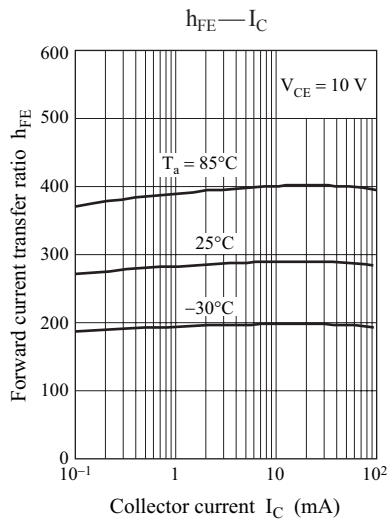
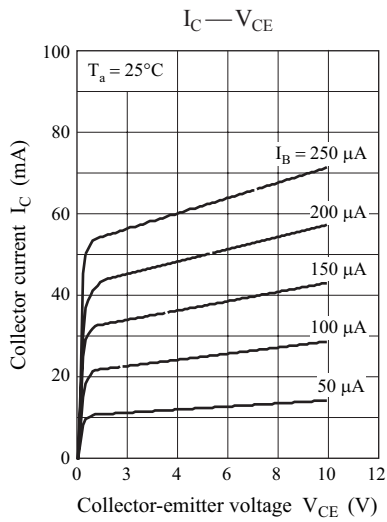
\*2: Ron measurement circuit



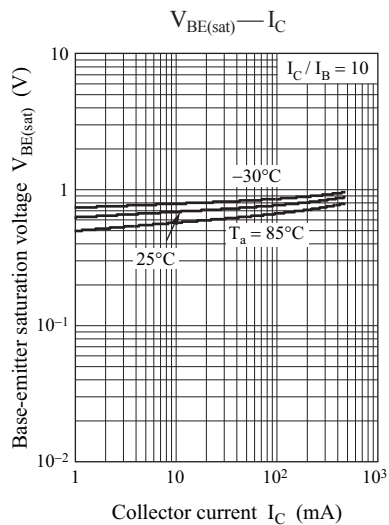
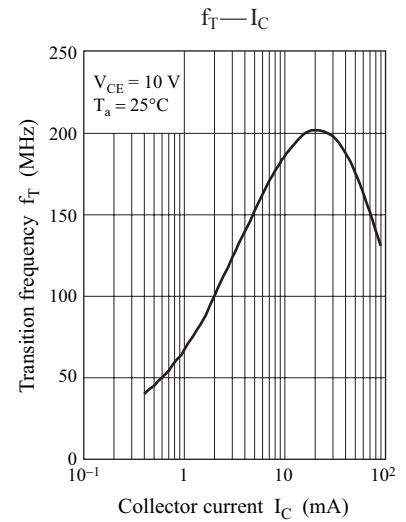
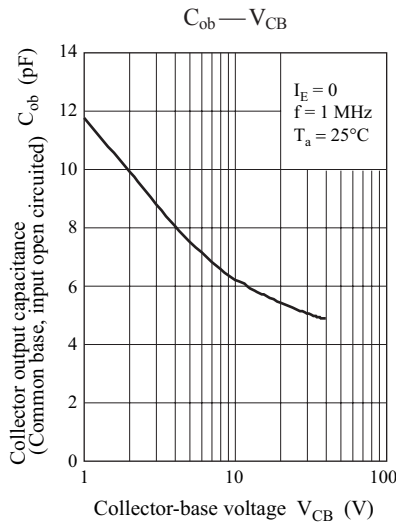
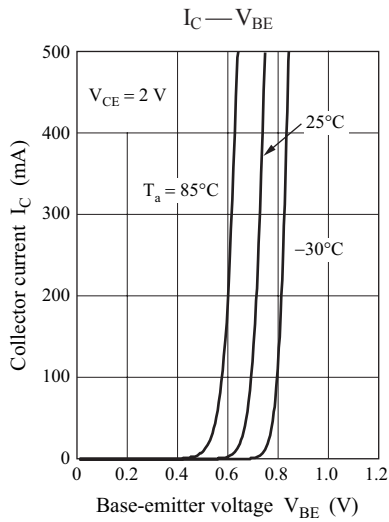
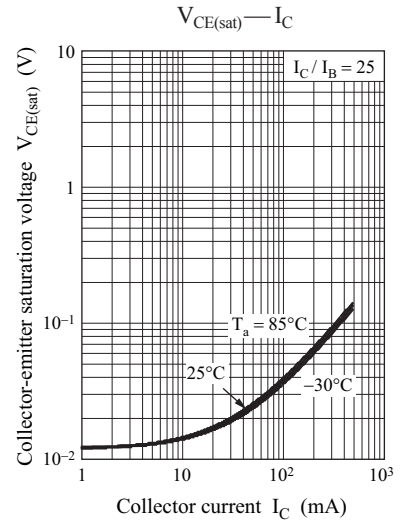
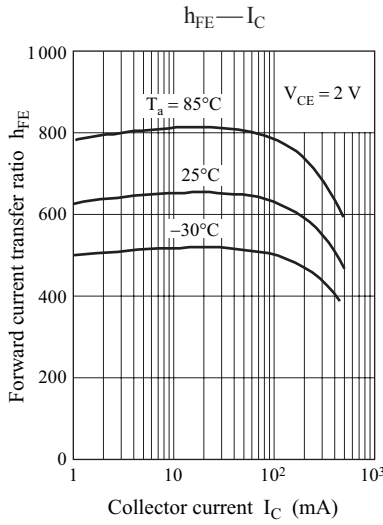
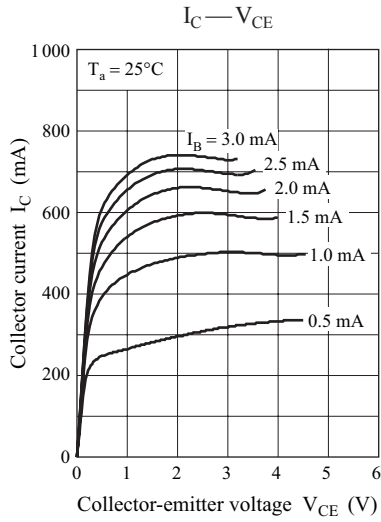
Common characteristics chart



Characteristics charts of Tr1

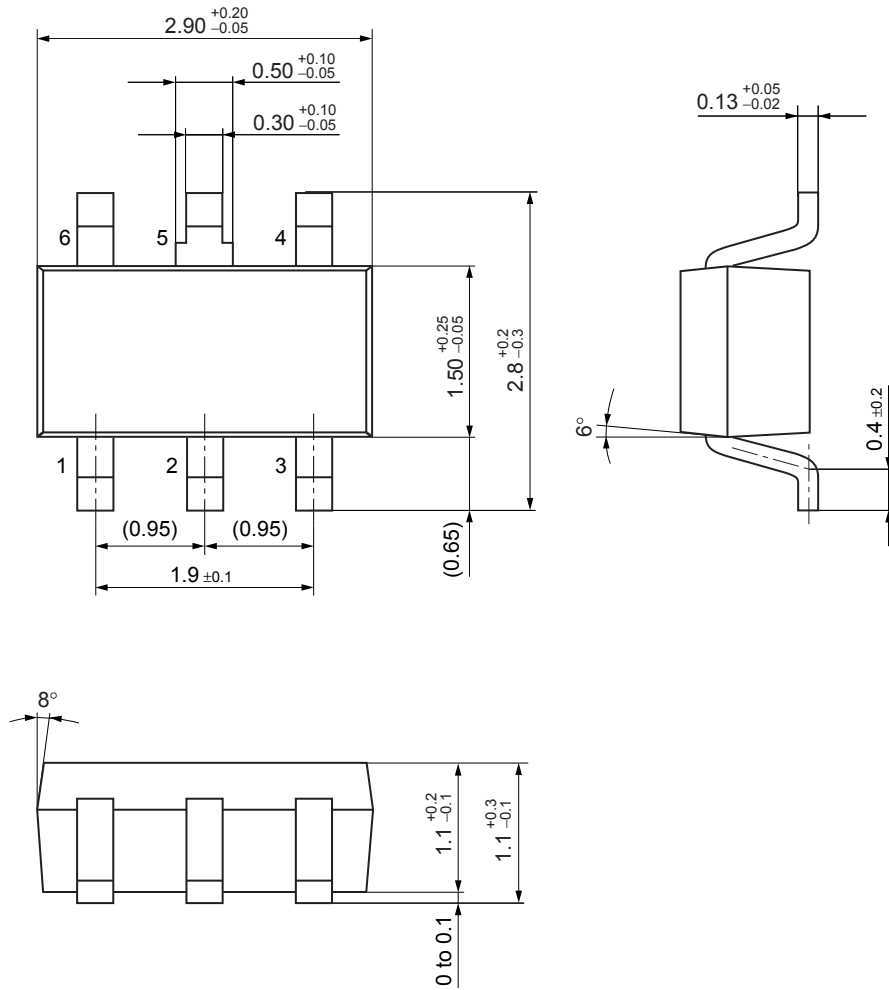


Characteristics charts of Tr2



Mini6-G4-B

Unit: mm



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